

APPLICATIONS

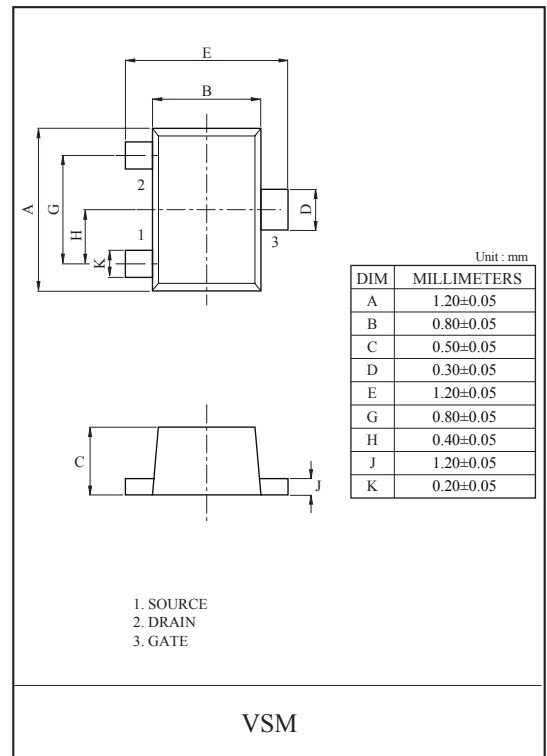
- Impedance converter applications.
- Infrared sensor.

FEATURES

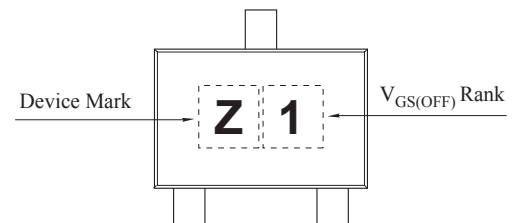
- Small I_{GSS} .
- Small C_{iss} .

MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-to-Source Voltage	V_{DSS}	20	V
Gate-to-Drain Voltage	V_{GDS}	-20	V
Gate-Drain Voltage	V_{GDO}	-20	V
Gate Current	I_G	10	mA
Drain Current	I_D	1	mA
Drain Power Dissipation	P_D	100	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55 ~ 150	°C



Marking Spec

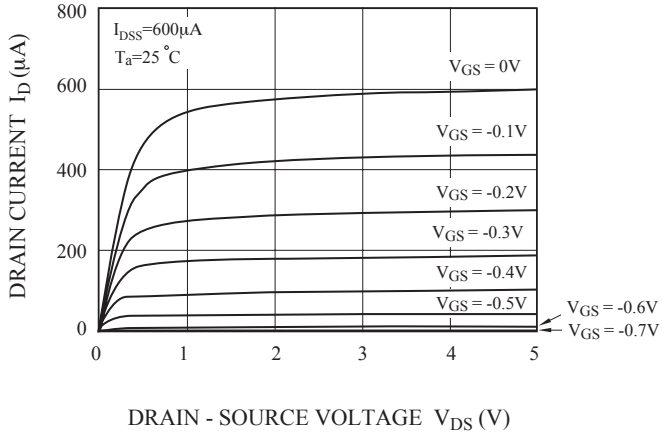


ELECTRICAL CHARACTERISTICS (Ta=25°C)

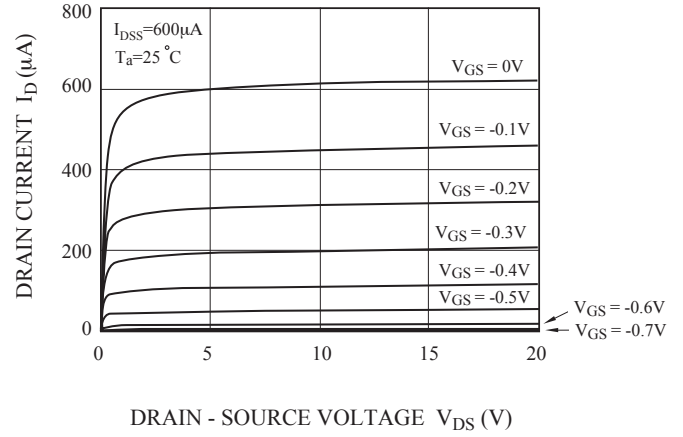
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate-Drain Breakdown Voltage	$V_{(BR)GDS}$	$I_D = -10\mu A$, $V_{DS} = 0$	-20	-	-	V
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = -20V$, $V_{DS} = 0$	-	-	-500	pA
Gate-Source Cut-off Voltage (Note)	$V_{GS(OFF)}$	$V_{DS} = 10V$, $I_D = 1\mu A$	-0.45	-	-1.0	V
Drain Current	I_{DSS}	$V_{DS} = 10V$, $V_{GS} = 0$	-	600	-	μA
Foward Transfer Admittance	$ y_{fs} $	$V_{DS} = 10V$, $V_{GS} = 0$, $f = 1kHz$	-	2.0	-	mS
Input Capacitance	C_{iss}	$V_{DS} = 10V$, $V_{GS} = 0$, $f = 1MHz$	-	2.0	-	pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = 10V$, $V_{GS} = 0$, $f = 1MHz$	-	1	-	pF
Source Voltage	V_S		-	0.6	-	V

*Note : $V_{GS(OFF)}$ Classification : A Rank(1) : -0.45V ~ -0.67V, B Rank(2) : -0.63V ~ -0.87V, C Rank(3) : -0.83V ~ -1.0V

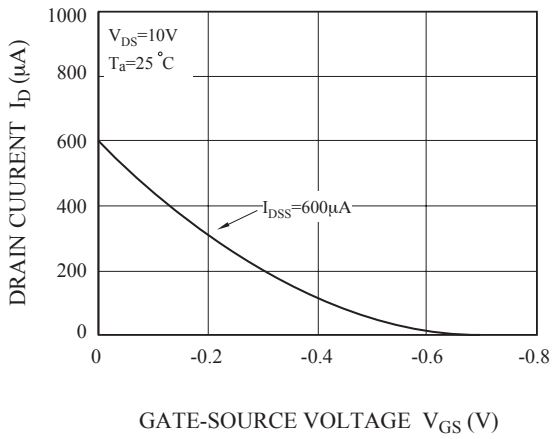
$I_D - V_{DS}$



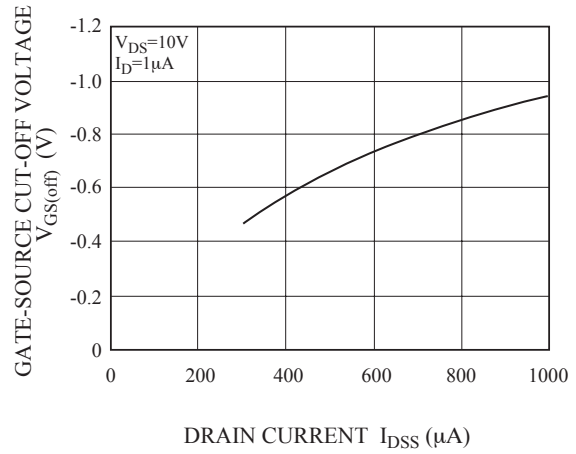
$I_D - V_{DS}$



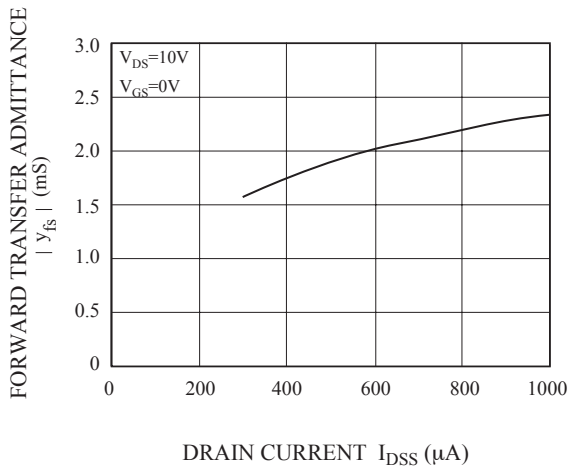
$I_D - V_{GS}$



$V_{GS(off)} - I_{DSS}$



$|y_{fs}| - I_{DSS}$



$P_D - T_a$

